

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14	(oxide (silicon near5 oxide)) same (polysilicon (poly near5 crystalline)) same (etch\$3 near5 selectivity)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 16:04
L2	14	(oxide (silicon near5 oxide)) same (polysilicon (poly near5 crystalline)) same selectivity	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 13:36
L3	3	(oxide (silicon near5 oxide)) near100 (polysilicon (poly near5 crystalline)) near100 selectivity	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 13:37
L4	3519	(oxide (silicon near5 oxide)) near100 (polysilicon silicon (poly near5 crystalline)) near100 selectivity	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 15:55
L5	341	4 and slurry	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 15:56
L6	1469	(oxide (silicon near5 oxide)) and (polysilicon silicon (poly near5 crystalline)) and selectivity	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/17 15:55
L7	57	6 and slurry	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/17 15:56
L8	44913	(CMP (chemical near5 mechanical near5 polish\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 16:05
L9	9102	8 and slurry	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 16:06
L10	5462	(438/689-695).CCLS.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/02/17 16:09
L11	1728	9 and 10	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/17 16:26